


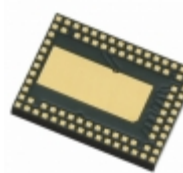
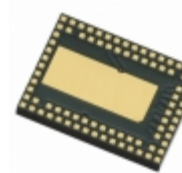

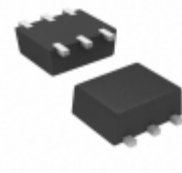


	<h2>SI1026X-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI1026X-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET 2N-CH 60V 0.305A SC89-6</p> <p>Datenblätter:  SI1026X-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 97296 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI1026X-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET 2N-CH 60V 0.305A SC89-6
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	97296 pcs Stock
Hersteller Standard Vorlaufzeit	33 Weeks
detaillierte Beschreibung	Mosfet Array 2 N-Channel (Dual) 60V 305mA 250mW
Serie	-
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	250mW
Verpackung / Gehäuse	SOT-563, SOT-666
Supplier Device-Gehäuse	SC-89-6
Typ FET	2 N-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	60V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	305mA
Rds On (Max) @ Id, Vgs	1.4 Ohm @ 500mA, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	0.6nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	30pF @ 25V
Verpackung	Tape & Reel (TR)
Basisteilenummer	SI1026
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI1026X-T1-GE3TR

SI1026X-T1-GE3 ist neu im Original, Suche SI1026X-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1026X-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI1026X-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI1026X-T1-E3 Vishay / Siliconix MOSFET 2N-CH 60V 0.305A SOT563F</p>	 <p>SI1027-A-GM Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>	 <p>SI1027-B-GM3 Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>	 <p>SI1027-B-GM3R Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>
 <p>SI1026X-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 60V 0.305A SOT563F</p>	 <p>SI1026X-T1-GE3 Vishay / Siliconix MOSFET 2N-CH 60V 0.305A SC89-6</p>	 <p>SI1027-A-GMR Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>	 <p>SI1026X VISHAY SI1026X VISHAY</p>

heiße Teile

Mehr

SI1022R-T1-E3	SI1022R-T1-E3	SI1022R-T1-GE3	D SI1022R-T1-GE3	SI1022R-T1-E3
SI1023CX-T1-GE3	SI1023CX-T1-GE3	D SI1023X-T1	SI1023X-T1-E3	SI1023X-T1-E3
SI1023X-T1-GE3	SI1023X-T1-GE3	SI1024-T1	SI1024X-T1	SI1024X-T1-E3
D SI1024X-T1-E3	SI1024X-T1-GE3	SI1024X-T1-GE3	SI1024X-T1-GE3	SI1025X-T1
SI1025X-T1-E3	SI1025X-T1-E3	SI1026X-T1	SI1026X-T1-E3	SI1026X-T1-E3
SI1026X-T1-GE3	SI1028X-T1-GE3	D SI1028X-T1-GE3	SI1029X-T1-GE3	SI1029X-T1-GE3
SI1031R-T1	D SI1031R-T1-E3	SI1031R-T1-E3	SI1031R-T1-GE3	SI1031R-T1-GE3
SI1031X-T1	SI1031X-T1-E3	SI1031X-T1-E3	SI1031X-T1-GE3	SI1031X-T1-GE3
SI1032R-T1	SI1032R-T1-E3	SI1032R-T1-E3	D SI1032R-T1-GE3	SI1032R-T1-GE3
SI1032X-T1	SI1032X-T1-E3	SI1032X-T1-E3	SI1032X-T1-GE3	SI1032X-T1-GE3

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